

# 10V Drive Nch MOSFET

## **R5016FNX**

#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) High ESD.

#### Application

Switching

#### Packaging specifications

	Package	Bulk
Type	Code	-
	Basic ordering unit (pieces)	500
R5016FNX	0	

#### ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{DSS}$	500	V
Gate-source voltage		$V_{GSS}$	±30	V
Drain current	Continuous	I <sub>D</sub> *3	±16	Α
	Pulsed	I <sub>DP</sub> *1	±64	Α
Source current	Continuous	I <sub>S</sub> *3	16	Α
(Body Diode)	Pulsed	I <sub>SP</sub> *1	64	Α
Avalanche current		I <sub>AS</sub> *2	8	Α
Avalanche energy		E <sub>AS</sub> *2 17.1		mJ
Power dissipation		P <sub>D</sub> *4	50	W
Channel temperature		$T_ch$	150	°C
Range of storage temperature		$T_{stg}$	-55 to +150	°C

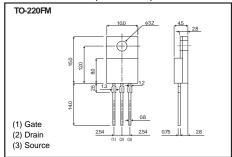
<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

#### • Thermal resistance

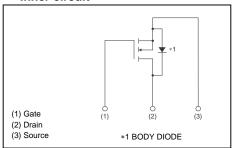
Parameter	Symbol	Limits	Unit
Channel to Case	R <sub>th (ch-c)</sub> *	2.5	°C/W

<sup>\*</sup> T<sub>C</sub>=25°C

#### • Dimensions (Unit : mm)



#### • Inner circuit



<sup>\*2</sup> L= 500 $\mu$ H, V<sub>DD</sub>=50V, R<sub>G</sub>=25 $\Omega$ , T<sub>ch</sub>=25°C

<sup>\*3</sup> Limited only by maximum channel temperature allowed.

<sup>\*4</sup> T<sub>C</sub>=25°C

# ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$		-	±100	nA	$V_{GS}$ =±30V, $V_{DS}$ =0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	500	-	-	V	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	1	-	100	μA	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	3.0	-	5.0	V	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA
Static drain-source on-state resistance	R <sub>DS (on)</sub>	-	0.25	0.325	Ω	I <sub>D</sub> =8A, V <sub>GS</sub> =10V
Forward transfer admittance	I Y <sub>fs</sub> I*	6.2	11	1	S	$V_{DS}$ =10V, $I_{D}$ =8A
Input capacitance	C <sub>iss</sub>		1700	-	pF	V <sub>DS</sub> =25V
Output capacitance	C <sub>oss</sub>	1	1000	1	рF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>		35	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	1	35	-	ns	V <sub>DD</sub> ≒250V, I <sub>D</sub> =8.0A
Rise time	t <sub>r</sub> *	1	60	1	ns	V <sub>GS</sub> =10V
Turn-off delay time	t <sub>d(off)</sub> *	1	110	-	ns	$R_L=31.25\Omega$
Fall time	t <sub>f</sub> *	-	35	-	ns	$R_G=10\Omega$
Total gate charge	Q <sub>g</sub> *	-	46	-	nC	V <sub>DD</sub> ≒250V
Gate-source charge	Q <sub>gs</sub> *	ı	11	-	nC	I <sub>D</sub> =8.0A
Gate-drain charge	Q <sub>gd</sub> *	-	19	-	nC	V <sub>GS</sub> =10V

<sup>\*</sup>Pulsed

## ●Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub> *	•	-	1.5	V	I <sub>S</sub> =16A, V <sub>GS</sub> =0V
Reverse recovery time	t <sub>rr</sub> *	75	100	125	ns	I <sub>S</sub> =16A, V <sub>GS</sub> =0V di/dt=100A/μs

<sup>\*</sup>Pulsed

#### ●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics ( I )

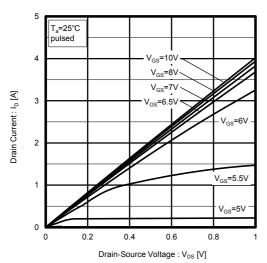


Fig.3 Typical Transfer Characteristics

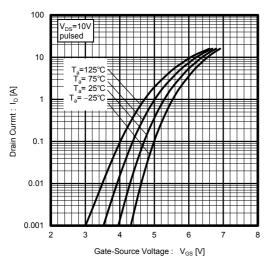
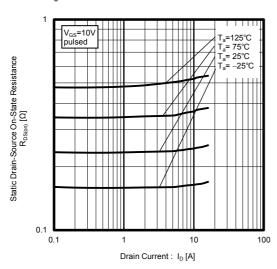


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current



Flg.2 Typical Output Characteristics ( II )

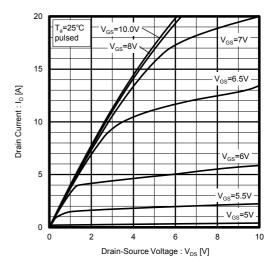


Fig.4 Gate Threshold Voltage vs. Channel Temperature

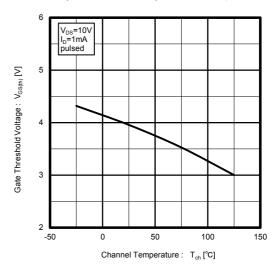


Fig.6 Static Drain-Source On-State Resistance vs. Channel Temperature

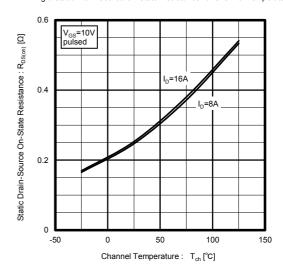


Fig.7 Forward Transfer Admittance vs. Drain Current

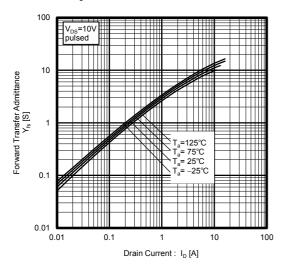


Fig.9 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

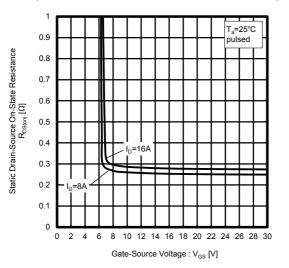


Fig.11 Dynamic Input Characteristics

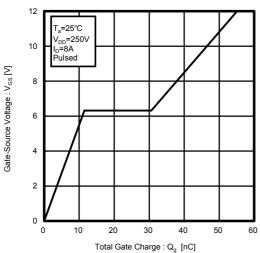


Fig.8 Source Current vs. Source-Drain Voltage

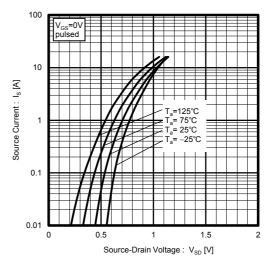


Fig.10 Switching Characteristics

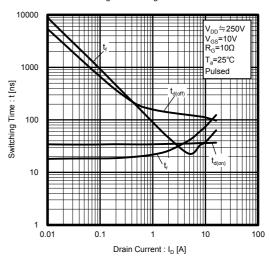


Fig.12 Typical Capacitance vs. Drain-Source Voltage

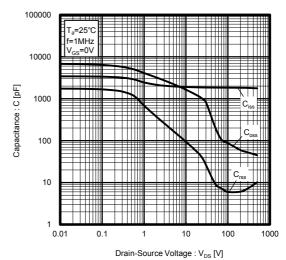
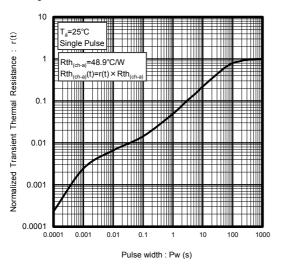


Fig.13 Normalized Transient Thermal Resistance v.s. Pulse Width



1000

100

100

100

P<sub>W</sub> = 100 $\mu$ s

10

Operation in this area is limited by R<sub>DS(on)</sub>

(V<sub>GS</sub> = 10V)

P<sub>W</sub> = 1 ms

is limited by R<sub>DS(on)</sub>

(V<sub>GS</sub> = 10V)

P<sub>W</sub> = 10ms

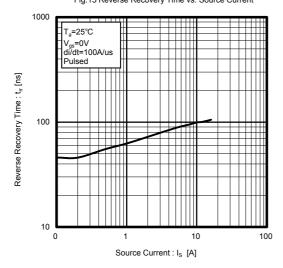
0.1

1 1 1 0 100 1000

Drain-Source Voltage : V<sub>DS</sub> [V]

Fig.14 Maximum Safe Operating Area

Fig.15 Reverse Recovery Time vs. Source Current



#### Measurement circuits

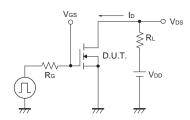


Fig.1-1 Switching Time Measurement Circuit

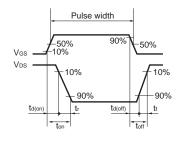


Fig.1-2 Switching Waveforms

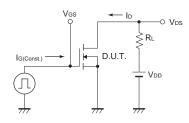


Fig.2-1 Gate Charge Measurement Circuit

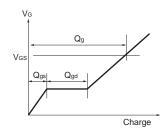


Fig.2-2 Gate Charge Waveform

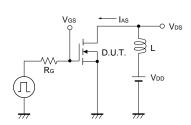


Fig.3-1 Avalanche Measurement Circuit

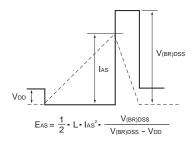


Fig.3-2 Avalanche Waveform

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